# BAT54SWT1G, NSVBAT54SWT1G

# Dual Series Schottky Barrier Diodes

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

#### Features

- Extremely Fast Switching Speed
- Low Forward Voltage 0.35 Volts (Typ) @  $I_F = 10 \text{ mAdc}$
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS** (T<sub>J</sub> = $125^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	30	V
Forward Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>F</sub>	200 1.6	mW mW/°C
Forward Current (DC)	١ <sub>F</sub>	200 Max	mA
Non–Repetitive Peak Forward Current $t_p < 10$ msec	I <sub>FSM</sub>	600	mA
Repetitive Peak Forward Current Pulse Wave = 1 sec, Duty Cycle = 66%	I <sub>FRM</sub>	300	mA
Junction Temperature	TJ	-55 to 125	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C
Electrostatic Discharge	ESD	HM < 8000 MM < 400	V V

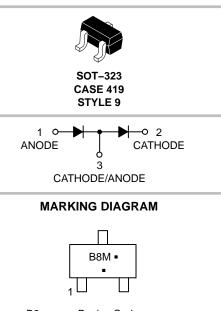
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



## **ON Semiconductor®**

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# 30 VOLT DUAL SERIES SCHOTTKY BARRIER DIODES



B8 = Device Code M = Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
BAT54SWT1G	SOT-323 (Pb-Free)	3,000 / Tape & Reel
NSVBAT54SWT1G	SOT-323 (Pb-Free)	3,000 / Tape & Reel

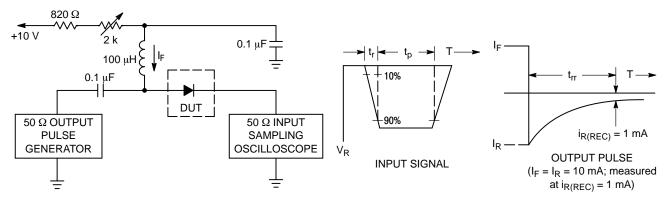
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# BAT54SWT1G, NSVBAT54SWT1G

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Breakdown Voltage $(I_R = 10 \ \mu A)$	V <sub>(BR)R</sub>	30	-	_	V
Total Capacitance (V <sub>R</sub> = 1.0 V, f = 1.0 MHz)	CT	_	7.6	10	pF
Reverse Leakage (V <sub>R</sub> = 25 V)	I <sub>R</sub>	_	0.5	2.0	μAdc
Forward Voltage (I <sub>F</sub> = 0.1 mAdc)	V <sub>F</sub>	_	0.22	0.24	Vdc
Forward Voltage (I <sub>F</sub> = 30 mAdc)	V <sub>F</sub>	_	0.41	0.5	Vdc
Forward Voltage (I <sub>F</sub> = 100 mAdc)	V <sub>F</sub>	_	0.52	0.8	Vdc
Reverse Recovery Time ( $I_F = I_R = 10 \text{ mAdc}, I_{R(REC)} = 1.0 \text{ mAdc}, Figure 1$ )	t <sub>rr</sub>	_	-	5.0	ns
Forward Voltage (I <sub>F</sub> = 1.0 mAdc)	V <sub>F</sub>	_	0.29	0.32	Vdc
Forward Voltage (I <sub>F</sub> = 10 mAdc)	V <sub>F</sub>	_	0.35	0.40	Vdc

### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted) (EACH DIODE)

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



Notes: 1. A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current (I<sub>F</sub>) of 10 mA. 2. Input pulse is adjusted so I<sub>R(peak)</sub> is equal to 10 mA. 3. t<sub>p</sub> » t<sub>rr</sub>

#### Figure 1. Recovery Time Equivalent Test Circuit

## BAT54SWT1G, NSVBAT54SWT1G

### **TYPICAL CHARACTERISTICS**

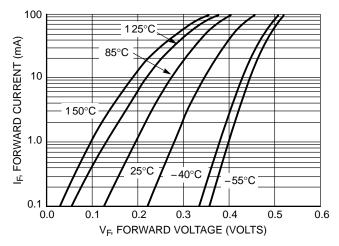


Figure 2. Forward Voltage

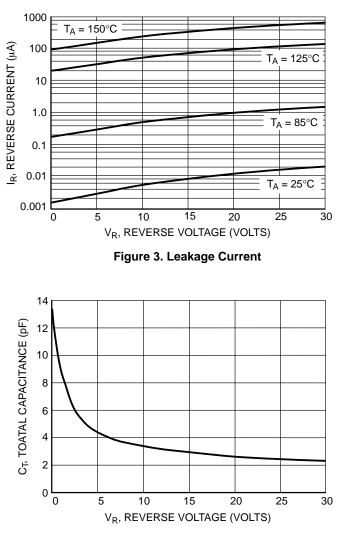
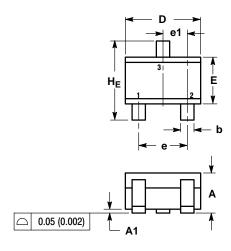


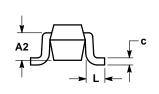
Figure 4. Total Capacitance

### BAT54SWT1G, NSVBAT54SWT1G

#### PACKAGE DIMENSIONS

SOT-323 (SC-70) CASE 419-04 ISSUE N





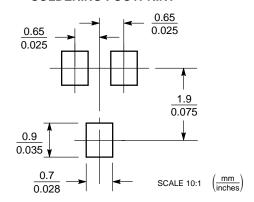
STYLE 9

PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE

NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
Е	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

SOLDERING FOOTPRINT\*



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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